

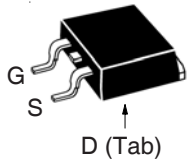
PolarP™ Power MOSFETs

P-Channel Enhancement Mode
Avalanche Rated

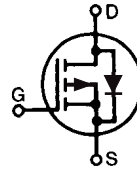
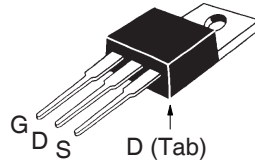
IXTA36P15P
IXTP36P15P
IXTQ36P15P
IXTH36P15P

$V_{DSS} = -150V$
 $I_{D25} = -36A$
 $R_{DS(on)} \leq 110m\Omega$

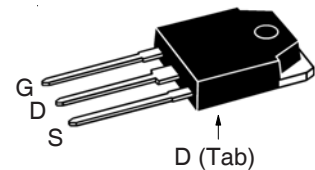
TO-263 AA (IXTA)



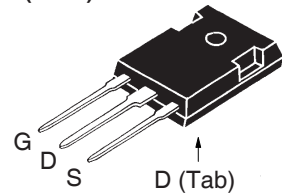
TO-220AB (IXTP)



TO-3P (IXTQ)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | - 150 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | - 150 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | - 36 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | - 90 | A |
| I_A | $T_C = 25^\circ C$ | - 36 | A |
| E_{AS} | $T_C = 25^\circ C$ | 1.5 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 10 | V/ns |
| P_D | $T_C = 25^\circ C$ | 300 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque (TO-3P, TO-220 & TO-247) | 1.13/10 | Nm/lb.in. |
| F_C | Mounting Force (TO-263) | 10..65/2.2..14.6 | N/lb. |
| Weight | TO-263 | 2.5 | g |
| | TO-220 | 3.0 | g |
| | TO-3P | 5.5 | g |
| | TO-247 | 6.0 | g |

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|------------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = -250 \mu A$ | - 150 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | - 2.5 | | - 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | -10 μA - 250 μA |
| $R_{DS(on)}$ | $V_{GS} = -10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 110 m Ω |

Features

- International Standard Packages
- Rugged PolarP™ Process
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low $R_{DS(ON)}$ and Q_G
- Low Drain-to-Tab Capacitance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-----------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = -10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 11 | 19 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$ | | 3100 | pF |
| C_{oss} | | | 610 | pF |
| C_{rss} | | | 100 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3.3\Omega$ (External) | | 21 | ns |
| t_r | | | 31 | ns |
| $t_{d(off)}$ | | | 36 | ns |
| t_f | | | 15 | ns |
| $Q_{g(on)}$ | $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 55 | nC |
| Q_{gs} | | | 20 | nC |
| Q_{gd} | | | 18 | nC |
| R_{thJC} | | | | 0.42 °C/W |
| R_{thCS} | (TO-3P, TO-247) | | 0.21 | °C/W |
| | (TO-220) | | 0.50 | °C/W |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|-------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | - 36 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | -140 A |
| V_{SD} | $I_F = -18\text{A}$, $V_{GS} = 0\text{V}$, Note 1 | | | - 3.3 V |
| t_{rr} | $I_F = -18\text{A}$, $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -75\text{V}$, $V_{GS} = 0\text{V}$ | | 228 | ns |
| Q_{RM} | | | 2.0 | μC |
| I_{RM} | | | -17.6 | A |

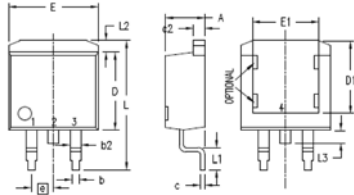
Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

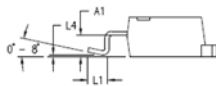
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

TO-263 Outline

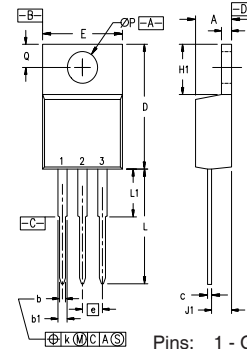


1 - Gate
2,4 - Drain
3 - Source



| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .160 | .190 | 4.06 | 4.83 |
| A1 | .080 | .110 | 2.03 | 2.79 |
| b | .020 | .039 | 0.51 | 0.99 |
| b2 | .045 | .055 | 1.14 | 1.40 |
| c | .016 | .029 | 0.40 | 0.74 |
| c2 | .045 | .055 | 1.14 | 1.40 |
| D | .340 | .380 | 8.64 | 9.65 |
| D1 | .315 | .350 | 8.00 | 8.89 |
| E | .380 | .410 | 9.65 | 10.41 |
| E1 | .245 | .320 | 6.22 | 8.13 |
| e | .100 BSC | | 2.54 BSC | |
| L | .575 | .625 | 14.61 | 15.88 |
| L1 | .090 | .110 | 2.29 | 2.79 |
| L2 | .040 | .055 | 1.02 | 1.40 |
| L3 | .050 | .070 | 1.27 | 1.78 |
| L4 | 0 | .005 | 0 | 0.13 |

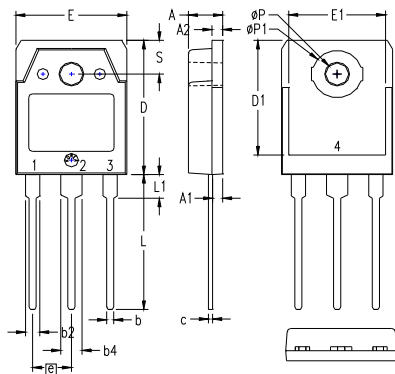
TO-220 Outline



Pins: 1 - Gate
2 - Drain
3 - Source

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .190 | 4.32 | 4.83 |
| b | .025 | .040 | 0.64 | 1.02 |
| b1 | .045 | .065 | 1.15 | 1.65 |
| c | .014 | .022 | 0.35 | 0.56 |
| D | .580 | .630 | 14.73 | 16.00 |
| E | .390 | .420 | 9.91 | 10.66 |
| e | .100 BSC | | 2.54 BSC | |
| F | .045 | .055 | 1.14 | 1.40 |
| H1 | .230 | .270 | 5.85 | 6.85 |
| J1 | .090 | .110 | 2.29 | 2.79 |
| k | 0 | .015 | 0 | 0.38 |
| L | .500 | .550 | 12.70 | 13.97 |
| L1 | .110 | .230 | 2.79 | 5.84 |
| ØP | .139 | .161 | 3.53 | 4.08 |
| Q | .100 | .125 | 2.54 | 3.18 |

TO-3P Outline

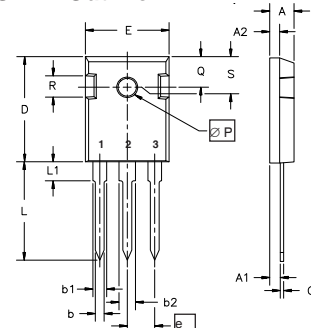


Pins: 1 - Gate 2,4 - Drain
3 - Source

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .185 | .193 | 4.70 | 4.90 |
| A1 | .051 | .059 | 1.30 | 1.50 |
| A2 | .057 | .065 | 1.45 | 1.65 |
| b | .035 | .045 | 0.90 | 1.15 |
| b2 | .075 | .087 | 1.90 | 2.20 |
| b4 | .114 | .126 | 2.90 | 3.20 |
| c | .022 | .031 | 0.55 | 0.80 |
| D | .780 | .791 | 19.80 | 20.10 |
| D1 | .665 | .677 | 16.90 | 17.20 |
| E | .610 | .622 | 15.50 | 15.80 |
| E1 | .531 | .539 | 13.50 | 13.70 |
| e | .215 BSC | | 5.45 BSC | |
| L | .779 | .795 | 19.80 | 20.20 |
| L1 | .134 | .142 | 3.40 | 3.60 |
| ØP | .126 | .134 | 3.20 | 3.40 |
| ØP1 | .272 | .280 | 6.90 | 7.10 |
| S | .193 | .201 | 4.90 | 5.10 |

All metal area are tin plated.

TO-247 Outline



Pins: 1 - Gate 2 - Drain
3 - Source

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ØP | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

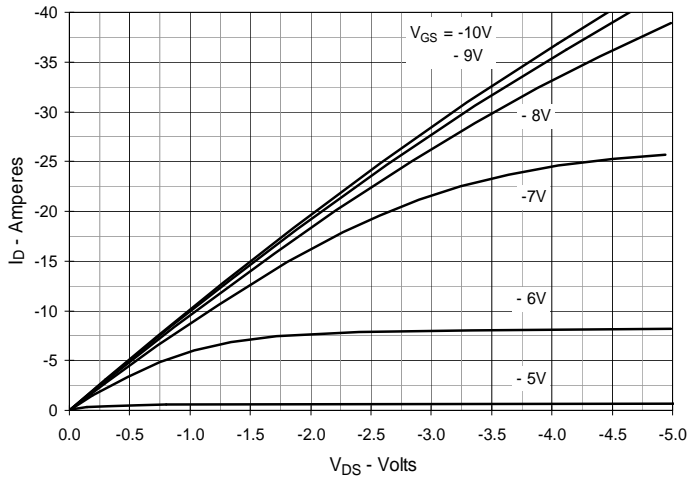


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

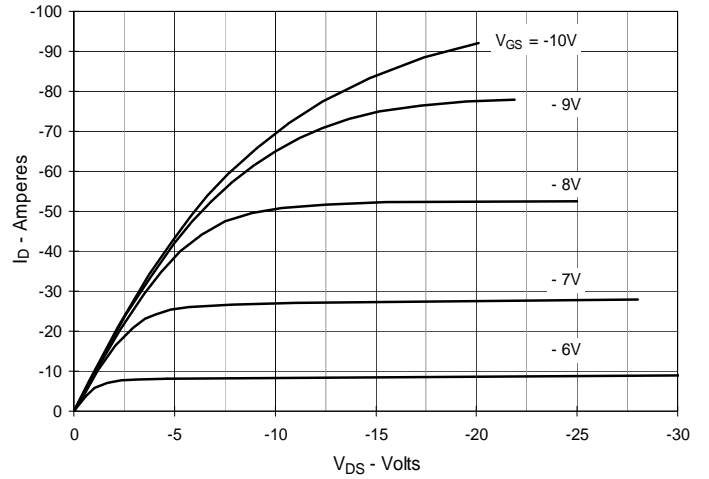


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

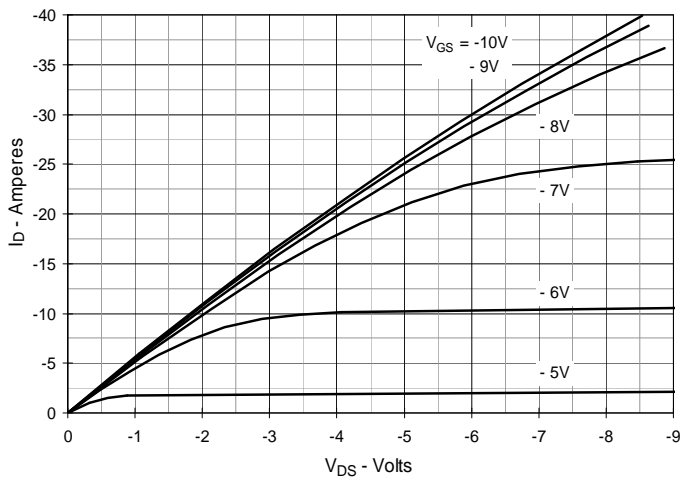


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -18\text{A}$ Value vs. Junction Temperature

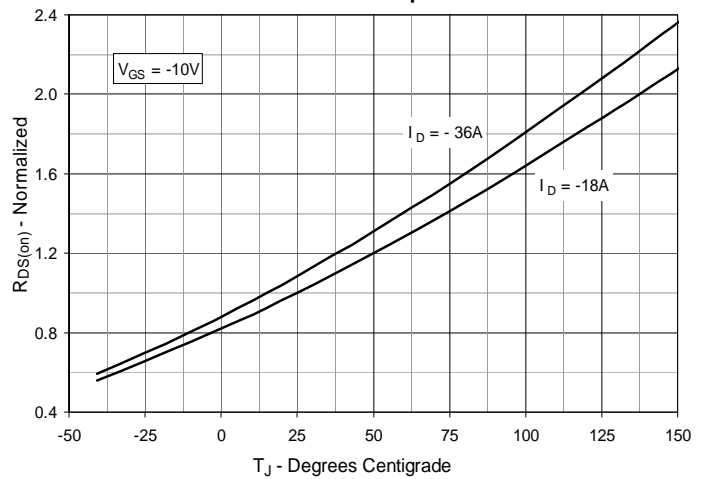


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -18\text{A}$ Value vs. Drain Current

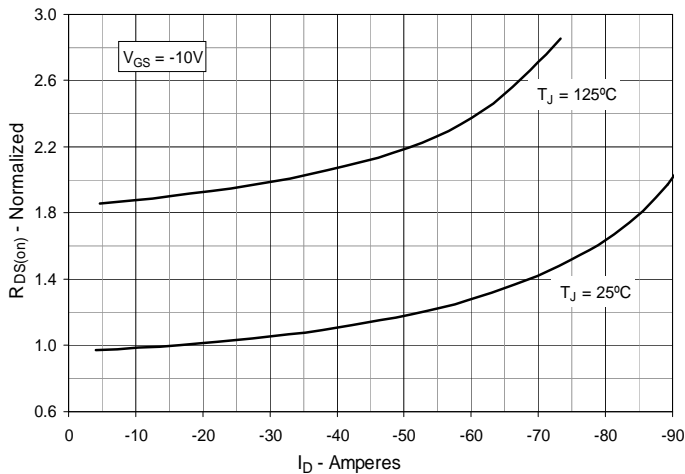


Fig. 6. Maximum Drain Current vs. Case Temperature

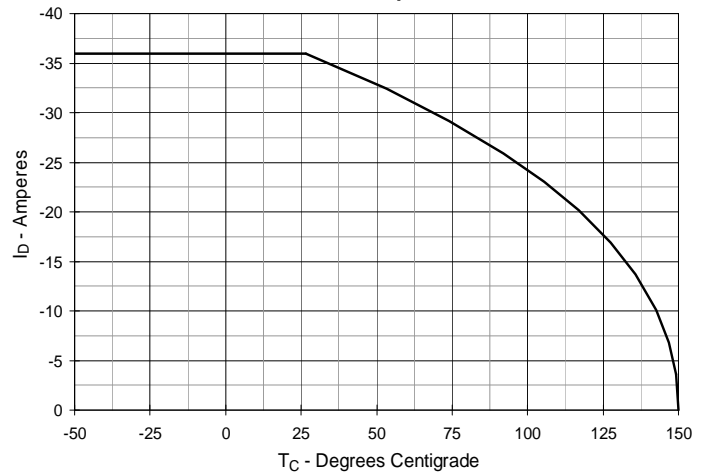


Fig. 7. Input Admittance

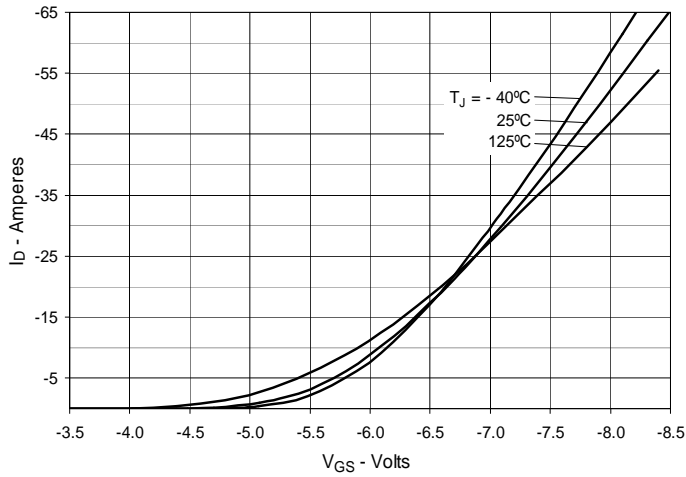


Fig. 8. Transconductance

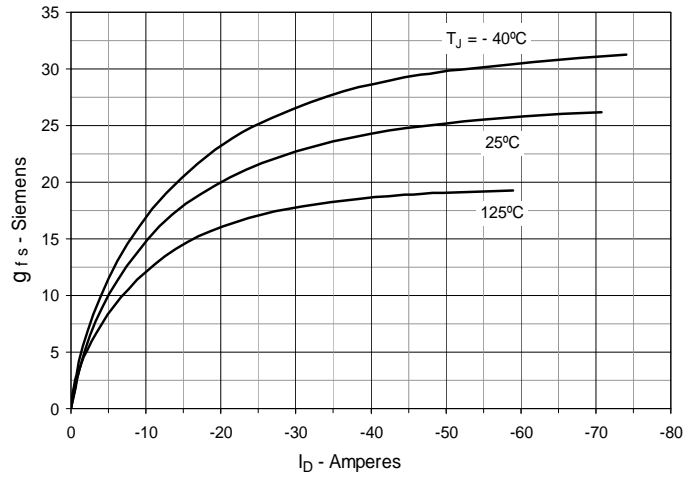


Fig. 9. Forward Voltage Drop of Intrinsic Diode

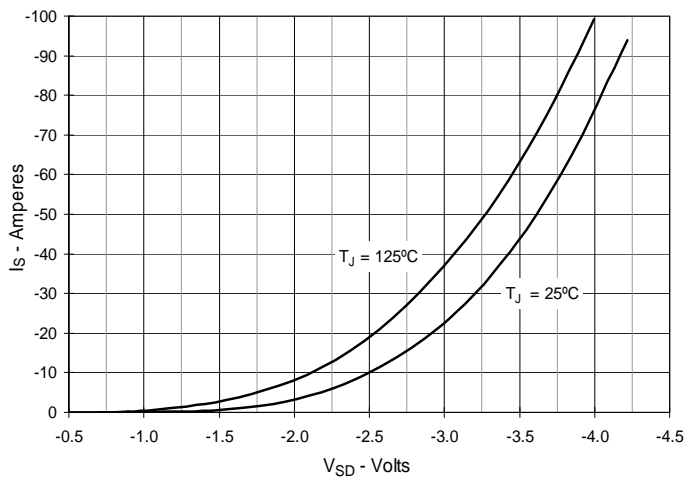


Fig. 10. Gate Charge

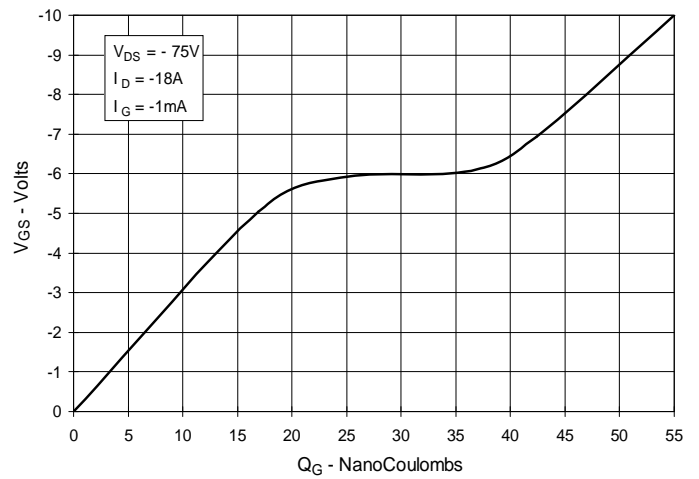


Fig. 11. Capacitance

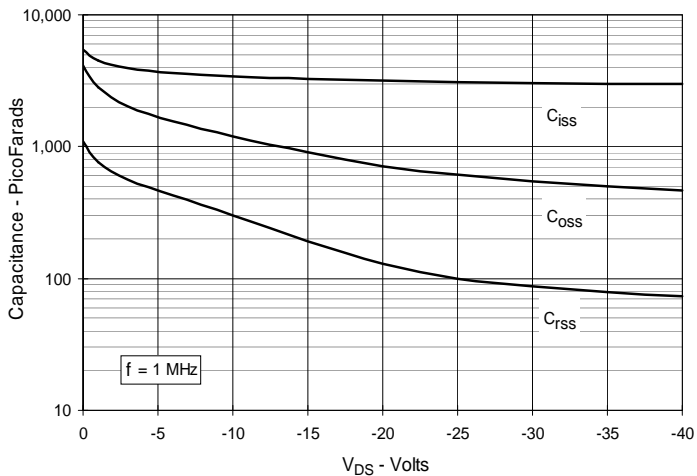


Fig. 12. Forward-Bias Safe Operating Area

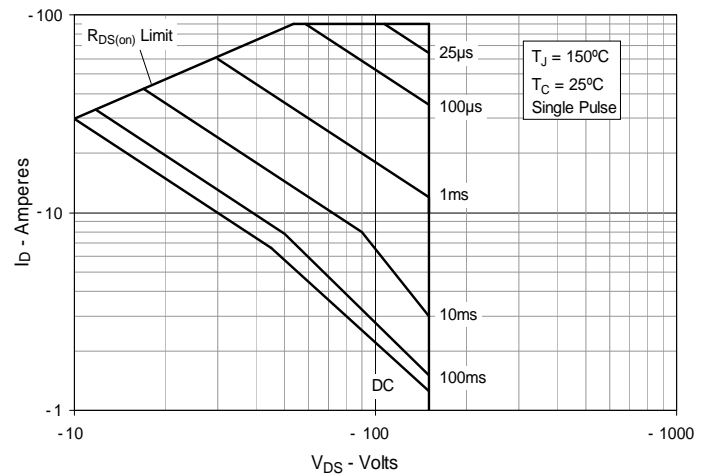
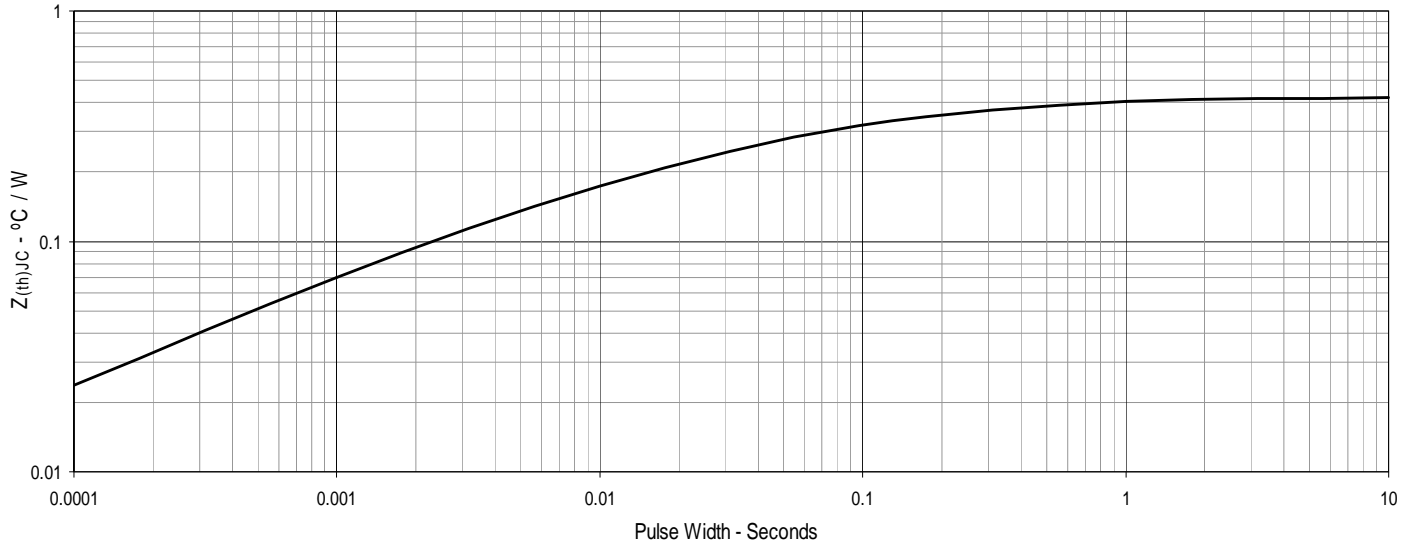


Fig. 13. Maximum Transient Thermal Impedance





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[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)